SHEET

Form PTO 1449 U.S. DEPARTMENT OF COMMERCE (Modified) PATENT AND TRADEMARK OFFICE			ATTY DOCKET NO. 211618US99	Y DOCKET NO.   SERIAL NO.   09/910,753				
			APPLICANT					
LIST OF REFERENCES CITED BY APPLICANT			Rudy M. EMRICK, et al.					
			FILING DATE GROUP					
				July 24, 2001 2826			_	
<u> </u>	U.S. PATENT DOCUMENTS							
EXAMINER DOCUMENT DATE		NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE			
11. 41	XN	6,233,435 B1	05/15/01	WONG				
79	хо	4,723,321	02/02/88	SALEH				
	ХP	6,181,920 B1	01/30/01	DENT ET AL				
	XQ	6,415,140 B1	07/02/02	BENJAMIN ET AL				
	XR	5,760,740	06/02/98	BLODGETT				
	xs	5,238,877	08/24/93	RUSSELL				
	хт	4,876,218	10/24/89	PESSA ET AL				
	ΧU	6,232,242 B1	05/15/01	HATA ET AL				
	ΧV	4,378,259	03/29/83	HASEGAWA ET AL				
	xw	6,278,541 B1	08/21/01	BAKER				
	ΧY	4,298,247	11/03/81	MICHELET ET AL				
	XZ	4,174,504	11/13/79	CHENAUSKY ET AL	TT			
	YA	3,758,199	09/11/73	THAXTER				
	YB	6,362,558 B1	03/26/02	FUKUI				
	YC	6,140,746	10/31/00	MIYASHITA ET AL	$\Box$			
	YD	2002/0076878 A1	06/20/02	WASA ET AL				
	YE	6,419,849 B1	07/16/02	QIU ET AL				
	YF	2002/0179000 A1	12/05/02	LEE ET AL				
	YG	6,341,851	01/29/02	TAKAYAMA ET AL				
	ΥH	2001/0055820 A1	12/27/01	SAKURAI ET AL				
	ΥI	6,204,525 B1	03/20/01	SAKURAI ET AL				
	YJ	5,985,404	11/16/99	YANO ET AL				
	ΥK	6,538,359 B1	03/25/03	HIRAKU ET AL			<del>-</del>	
	YL	6,498,358 B1	12/24/02	LACH ET AL				
	YM	5,387,811	02/07/95	SAIGOH				
	YN	5,523,602	06/04/96	HORIUCHI ET AL				
V	YO	5,362,998	11/08/94	IWAMURA ET AL				
1.7.	Y\$	5,188,976	02/23/93	KUME ET AL				
Examiner A a c				s of	Date Co		2/2/04	
*Examiner/Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in								

RECEIVED

JAN 20 2004

FECHNOLOGY CENTER 2800

**BEST AVAILABLE COPY** 

OTPE

SHEET 2 OF 4

Form PTO 1449 U.S. DEPARTMENT OF COMMERCE (Modified) PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 211618US99 SERIAL NO. 09/910,753  APPLICANT					
		211618US99 09/910,753					
LIST OF REFERENCES CITED BY APPLICANT			Rudy M. EMRICK, et al.				
			FILING DATE GROUP				
				July 24, 2001	1 2826		
				U.S. PATENT DOCUMENTS			
EXAMINER DOCUMENT DATE NUMBER		NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
1.7	YQ	6,501,121 B1	12/31/02	YU ET AL			
1	YR	5,919,515	07/06/99	YANO ET AL			
	YS	5,238,877	08/24/93	RUSSELL			
	YT	5,540,785	07/30/96	DENNARD ET AL			
	YU	5,997,638	12/07/99	COPEL ET AL			
	W	6,291,866	09/18/01	WALLACE			
	YW	5,365,477	11/15/94	COOPER, JR ET AL			
	YX	5,548,141	08/20/96	MORRIS ET AL		T	
	YY	2002/0021855	02/21/02	КІМ		TT	
	YZ	6,110,840	08/29/00	YU	T	$I^{-}$	
	ZA	5,667,586	09/16/97	EK ET AL			
	ZB	5,313,058	05/17/94	FRIEDERICH ET AL			
	zc	5,315,128	05/24/94	HUNT ET AL		1	
	ZD	5,919,522	07/06/99	BAUM ET AL	$T^{-1}$		
	ZE	4,843,609	06/27/89	OHÝA ET AL	TT		EC.
	ZF	4,626,878	12/02/86	KUWANO ET AL	T	1. [	1911
	ZG	4,525,871	06/25/85	FOYT ET AL	$T^{T}$		7. 7. 1.
	ZH	3,818,451	06/18/74	COLEMAN		17	10 A
	Zi	6,059,895	05/09/00	CHU ET AL	1 /	17	G O M
	ZJ	4,447,116	05/08/84	KING ET AL	$\top T$		VEC.
	ZK	6,022,671	02/08/00	BINKLEY ET AL			to de
	ZL	5,754,714	05/19/98	SUZUKI ET AL		١	
	ZM	6,524,651 B2	02/25/03	GAN ET AL		11,	-
	ZN	6,355,945 B1	03/12/03	KADOTA ET AL		T	
	zo	5,642,371	06/24/97	TOHYAMA ET AL			
	ZP	6,445,724 B2	09/03/02	ABELES			
	ZQ	5,753,934	05/19/98	YANO ET AL			
	ZR	6,326,667 B1	12/04/01	SUGIYAMA ET AL			
	zs	6,051,874	04/18/00	MASUDA	TT		
1	ZT	5,166,761	11/24/92	OLSON ET AL			
91.7	ZU	5,574,744	11/12/96	GAW ET AL	$\Box$		
Examiner			-		Date C	onsidered	212104
*Examiner: (	nitial if r	reference is considered,	whether or no	t citation is in conformance with MPEP to with next communication to applicant.	609; Draw	line through	h citation if not in

JAN 1 4 2004 SHEET 3 OF 4

Form PTO 1449 U.S. DEPARTMENT OF COMMERCE (Modified) PATENT AND TRADEMARK OFFICE		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO.	SERIAL NO.			
				211618US99	09/910,753			
		ATTY DOCKET NO. 211618US99 SERIAL NO. 09/910,753 APPLICANT						
LIST OF REFERENCES CITED BY APPLICANT			PLICANT	Rudy M. EMRICK, et al.				
				FILING DATE	GROUP			
·				July 24, 2001	2826			
FOREIGN PATENT DOCUMENTS								
		DOCUMENT		COLUNTOV	TRANSLATION			
		NUMBER DATE		COUNTRY	YES NO			
9.00	CCA	5-238894	09/17/93	JAPAN W/ENGLISH ABSTRACT				
	ССВ	2 152 315	07/31/85	GREAT BRITAIN				
	ccc	2001-196892	07/19/01	JAPAN W/ENGLISH ABSTRACT				
	CCD	2000-278085	10/06/00	JAPAN (ENGLISH ABSTRACT)				
	CCE	WO 03/012874	02/13/03	WIPO				
_	CCF	1 043 427	10/11/00	EUROPE				
	CCG	1 069 605	01/17/01	EUROPE				
	ССН	WO 02/099885	12/12/02	WIPO				
	CCI	10-269842	10/09/98	JAPAN W/ENGLISH ABSTRACT				
<del></del>	CCJ	59066183	04/14/84	JAPAN (ENGLISH ABSTRACT)				
<del></del>	ССК	03046384	02/27/91	JAPAN (ENGLISH ABSTRACT)				
<del></del>			02/07/02	WIPO				
<del></del>	CCL	WO 02/11254		EUROPE				
	ССМ	0 494 514	07/15/92					
	CCN	0 247 722	12/02/87	EUROPE				
	cco	1 037 272	09/20/00	EUROPE				
	CCP	59-073498	04/25/84	JAPAN (ENGLISH ABSTRACT)				
/_	cco	60-161635	08/23/85	JAPAN WÆNGLISH ABSTRACT				
4/	CCR	59-044004	03/12/84	JAPAN W/ENGLISH ABSTRACT				
1.6	ccs	0 392 714	10/17/90	EUROPE				
	ССТ							
	CCU							
	ccv							
	ccw							
	CCX							
	CCY			;	454			
	CCZ				1, Ci			
	CDA				<b>3</b>			
	CDB							
	CDC				₹ 22 Fri			
	CDD				C TOTAL			
	CDE				70 FD			
	CDF				22			
	CDG				800			
	CDH							
	CDI							
	CDJ							
	CDK	· · · · · · · · · · · · · · · · · · ·						
	CDL							
	СДМ							
	CDN	<u>.</u>						

			l	- IAN 4 / 2004	10. 10. 	SHEET	4	OF	4		
Form PTO 1449	·	U.S. DEPARTMENT OF COMMERCE	ATTY DOCKET	<u>9 JAR   4 2004</u> ₩	Š SE	RIAL NO.					
(Modified)		DATENT AND TRADEMARK OFFICE	211618US99	<b>E</b> 19	09/	910,753					
LIST OF REFERENCES CITED BY APPLICANT			APPLICANT	MADEMARI	<u></u>						
			Rudy M. EMRICK, et al.								
			FILING DATE GROUP								
			July 24, 2001		282	26					
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)											
Peter Weiss; "Speed demon gets hooked on silicon"; Science News Online; Sept. 15, 2001; pp. 1-3											
7-71	LLAB	"Motorola Develops New Super-Fast Chip"; USA Today; Sept. 4, 2001									
	LLAC	Lori Valigra; "Motorola Lays GaAs on Si Wafer"; AsiaBizTech; Nov. 2001pp. 1-3									
	LLAD	"Holy Graill Motorola Claims High-Yield GaAs Breakthrough"; Micromagazine.com (no date available); pp. 1-3									
	LLAE	Jong-Gul YOON; "Growth of Ferroelectric LINbO3 Thin Film on MgO-Buffered Si by the Sol-Gel Method"; Journal of the Korean Physical Society (Proc. Suppl.); Vol. 29, Nov. 1996; pp. S648-S651									
	LLAF	V. Bornand et al.; "Deposition of LiTaO3 thin films by pyrosol process"; Thin Solid Films 304 (1997); pp.239-244									
	LLAG	R. Droopad et al.; "Development of high dielectric constant epitaxial oxides on silicon by molecular beam epitaxy"; Materials Science and Engineering B87 (2001); pp.292-296									
	LLAH	A.K. Sharma et al.; "Integration of Pb(Zr0.52Ti0.48)O3 epilayers with Si by domain epitaxy"; Applied Physics Letters, Vol. 76, No. 11; March 13, 2000; pp. 1458-1460									
	LLAI	Dwight C. Streit et al; "High Reliability GaAs-AlGaAs HBT's by MBE with Be Base Doping and InGaAs Emitter Contacts"; 8179 leee Electron Device Letters; 12(1991) September, No. 9, New York, US									
	LLAJ	C. Y. Hung et al; "Piezoelectrically induced stress tuning of electro-optic devices"; 320 Applied Physics Letters; 59(1991) 30 December, No. 27, New York, US									
	LLAK	J. Piprek; "Heat Flow Analysis of Long-Wvelength VCSELs with Various DBR Materials"; University of Delaware, Materials Science, Newark, DE, 19716-3106; Oct. 31, 1994; pp. 286-287									
	LLAL	P. Mackowiak et al.; "Some aspects of designing an efficient nitride VCSEL resonator"; J. Phys. D: Appl. Phys. 34(2001); pp. 954-958									
	LLAM	M.R. Wilson et al.; GaAs-On-Si: A GaAs IC Manufacturer's Perspective*; GaAs IC Symposium, IEEE, 1988; pp. 243-246									
	LLAN	Y. Kitano et al.; "Thin film crystal growth of BaZrO3 at low oxygen partial pressure"; Journal of Crystal Growth 243 (2002); pp. 164-169									
1.7.	LLAO	M.E. Hawley; et al; "Microstructural Study of Colossal Magneto-Resistive Films As a Function of Growth Temperature, As Deposited and Annealed"; 401, 1996; pp. 531-536									
	LLAP										
	LLAQ										
Examiner	_		· a on	h	Date Consid	0	12	-/01	1		
*Examiner:/r	Examiner Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in										